

preliminary

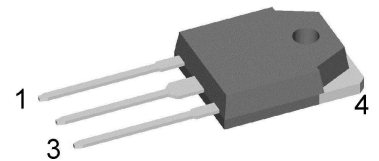
Sonic Fast Recovery Diode

V_{RRM}	=	600 V
I_{FAV}	= 2x	10 A
t_{rr}	=	35 ns

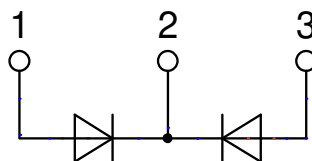
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DHG20C600QB



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-3P

- Industry standard outline compatible with TO-247
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

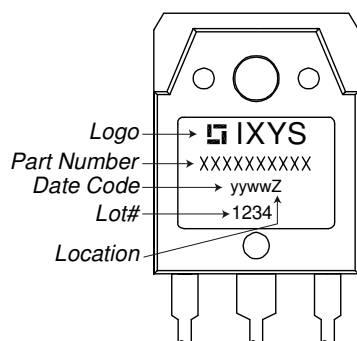
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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			15	μA
		V _R = 600 V	T _{VJ} = 125°C			1.2	mA
V _F	forward voltage drop	I _F = 10 A	T _{VJ} = 25°C			2.22	V
		I _F = 20 A				3.12	V
		I _F = 10 A	T _{VJ} = 125°C			2.17	V
		I _F = 20 A				3.27	V
I _{FAV}	average forward current	T _C = 95°C rectangular d = 0.5	T _{VJ} = 150°C			10	A
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.04	V
r _F	slope resistance					104	mΩ
R _{thJC}	thermal resistance junction to case					1.8	K/W
R _{thCH}	thermal resistance case to heatsink				0.3		K/W
P _{tot}	total power dissipation	T _C = 25°C				70	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		80	A
C _J	junction capacitance	V _R = 400 V f = 1 MHz		T _{VJ} = 25°C	6		pF
I _{RM}	max. reverse recovery current	} I _F = 10 A; V _R = 400 V -di _F /dt = 200 A/μs		T _{VJ} = 25 °C	4		A
				T _{VJ} = °C	tbd		A
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	35		ns
				T _{VJ} = °C	tbd		ns

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Package TO-3P			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			50	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				5		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking



Part description

D = Diode
 H = Sonic Fast Recovery Diode
 G = extreme fast
 20 = Current Rating [A]
 C = Common Cathode
 600 = Reverse Voltage [V]
 QB = TO-3P (3)

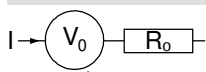
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG20C600QB	DHG20C600QB	Tube	30	503856

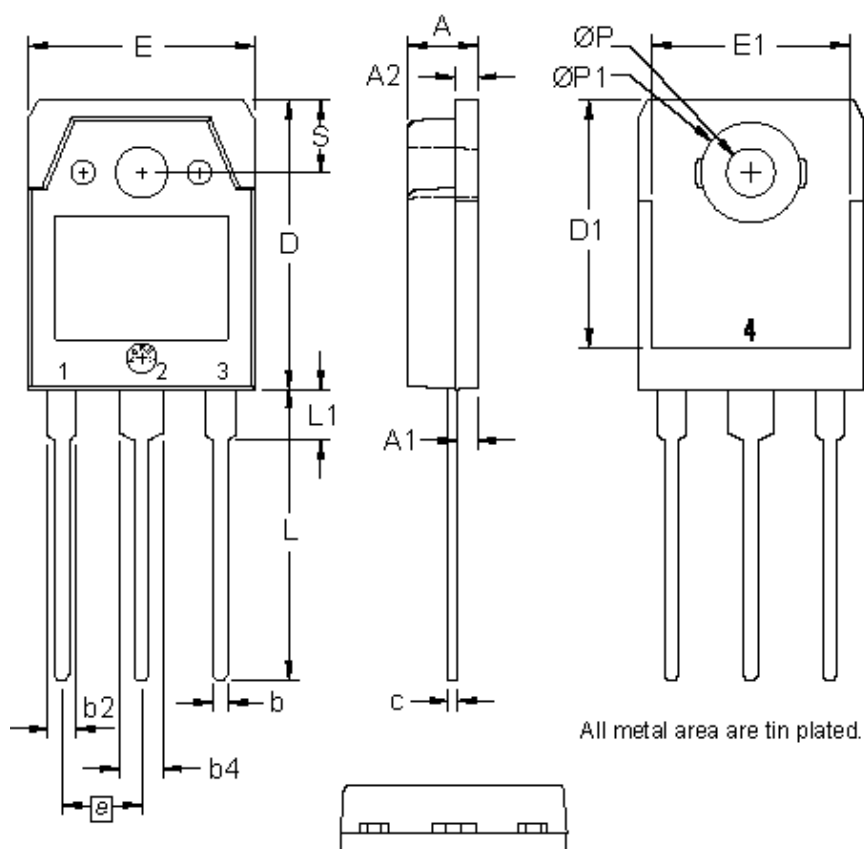
Similar Part	Package	Voltage class
DHG20C600PB	TO-220AB (3)	600

Equivalent Circuits for Simulation

* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

		Fast Diode	
$V_{0\max}$	threshold voltage	1.04	V
$R_{0\max}$	slope resistance *	101	mΩ

Outlines TO-3P


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	4.90	0.185	0.193
A1	1.30	1.50	0.051	0.059
A2	1.45	1.65	0.057	0.065
b	0.90	1.15	0.035	0.045
b2	1.90	2.20	0.075	0.087
b4	2.90	3.20	0.114	0.126
c	0.55	0.80	0.022	0.031
D	19.80	20.10	0.780	0.791
D1	16.90	17.20	0.665	0.677
E	15.50	15.80	0.610	0.622
E1	13.50	13.70	0.531	0.539
e	5.45 BSC		0.215 BSC	
L	19.80	20.20	0.780	0.795
L1	3.40	3.60	0.134	0.142
Ø P	3.20	3.40	0.126	0.134
ØP1	6.90	7.10	0.272	0.280
S	4.90	5.10	0.193	0.201

